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**TUTORIAL TOPIC:**

Epitaxy of III-nitride heterostructures: Growth & Fabrication

**TUTORIAL:**

In this tutorial, epitaxial growth of III-nitrides would be explained with particular focus on the two primary growth techniques commonly used – metal organic chemical vapor deposition (MOCVD) and molecular beam epitaxy (MBE).

Growth diagrams for MBE growth of both Ga-polar and N-polar GaN and InN would be explained along with details of growth of InGaN and InAlN based heterostructures.

MOCVD growth of III-nitrides on sapphire, SiC as well as on silicon would be covered in comprehensive details in this tutorial too.

**PROFILE:**

**EDUCATION:**

- PhD, Electrical Engineering, 2013, The Ohio State University, Columbus, USA.
- B. E. (Hons), Electrical & Electronics Engineering, 2008, Birla Institute of Technology and Science (BITS), Pilani.

**EXPERIENCE:**

- Postdoctoral researcher, The Ohio State University, Columbus, USA, October 2013 - July 2014
- Assistant Professor, IISc, Bangalore, August 2014 – present.